

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination	
	10/721,065	STRASSBURG ET AL.	
	Examiner	Art Unit	Page 1 of 1
	Savitri Mulpuri	2812	

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-4,234,554	11-1980	Rabenau et al.	423/409
*	B	US-4,851,302	07-1989	Nakagawa et al.	428/658
*	C	US-5,068,204	11-1991	Kukimoto et al.	117/93
*	D	US-5,786,269	07-1998	Murakami et al.	438/603
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Honda et al, "fromation of highly conductive p-type ZnSe using lithium nitride diffusion"Jpn Appl Phys,Vol.35(no.7) p3878-9(apr 1998)
*	V	Kijima et al, "Optimized ZnSe:N/ZnTe:N contact strcuture of ZnSebased II-V laser diodes Vol.73(no.2)p235-7(apr 23 a9998)I
*	W	Lim et al "High p-type doping of ZnSe using lithium nitride diffusion" applied Physcls Letters Vo.65(no.19) p2437-8(nov 7, 1994)
*	X	Kato et al, "Significant progress in II-VI blue green laser diod life time" Electronic Letters vol.34(no.3) p282-284(Feb 5, 1998)

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.